Fundamental description of (field induced) Josephson junctions coupling with semiconductor position based electrostatic qubits

Krzysztof Pomorski¹, Pawel Peczkowski², Panagiotis Giounanlis¹, Elena Blokhina 1 , Bogdan Staszewski 1 , Dirk Leipold 3

> 1: University College Dublin 2: Cardinal Stefan Wyszynki University in Warsaw 3: EQUAL 1, California kdvpomorski@gmail.com

July 11, 2019

K.P. P.P. ... B.S. (UCD) US vs semiconductor qubits July 11, 2019 1/23

つひい

[First Section](#page-2-0)

- [Essence of Josephson junction](#page-2-0)
- **[Andreev Bound State](#page-3-0)**

2 [Field induced Josephson junction](#page-5-0)

- 3 [Position based semiconductor devices](#page-6-0)
- [Interface between semiconductor qubit and Josephson junction](#page-14-0)

4 0 8

 Ω

Essence of Josephson effct

B J.

4 0 8

Josephson Junction

4 0 F

K.P. P.P. ... B.S. (UCD) **July 11, 2019** 5/23

化重 经间

 Ω

重 K.P, P.P, .., B.S (UCD) [JJs vs semiconductor qubits](#page-0-0) July 11, 2019 6 / 23

Concept of position based semiconductor qubit

э K.P, P.P, .., B.S (UCD) [JJs vs semiconductor qubits](#page-0-0) July 11, 2019 7 / 23

J.

K ロ ▶ K 御 ▶ K 君 ▶ K 君

The Hamiltonian of this system is given as

$$
\hat{H}(t) = \begin{pmatrix} E_{p1}(t) & t_{s12}(t) \\ t_{s12}^{\dagger}(t) & E_{p2}(t) \end{pmatrix}_{[x=(x_1,x_2)]} = (E_1(t) |E_1\rangle_t \langle E_1|_t + E_2(t) |E_2\rangle \langle E_2|)_{[E=(x_1,x_2)]}
$$
\nThe Hamiltonian $\hat{H}(t)$ eigenenergies $E_1(t)$ and $E_2(t)$ with $E_2(t) > E_1(t)$ are given as

\n
$$
\tag{1}
$$

$$
E_1(t) = \left(-\sqrt{\frac{(E_{p1}(t) - E_{p2})^2}{4} + |t_{s12}(t)|^2} + \frac{E_{p1}(t) + E_{p2}(t)}{2}\right),
$$

\n
$$
E_2(t) = \left(+\sqrt{\frac{(E_{p1}(t) - E_{p2})^2}{4} + |t_{s12}(t)|^2} + \frac{E_{p1}(t) + E_{p2}(t)}{2}\right),
$$
 (2)

K.P, P.P, .., B.S. (UCD) [JJs vs semiconductor qubits](#page-0-0) July 11, 2019 8/23

K ロ ▶ K 御 ▶ K 舌

 \rightarrow ≃

Having Hermitian matrix \hat{A} with real valued coefficients $a_{11}(t)$, $a_{22}(t)$, $a_{12r}(t)$, $a_{12i}(t)$ we observe that

$$
\hat{A}_{2\times 2} = \begin{pmatrix} a_{11} & a_{12r} + ia_{12i} \\ a_{12r} - ia_{12i} & a_{22} \end{pmatrix},
$$
 (3)

4 D F

$$
\exp(\frac{1}{\hbar i}\hat{A}_{2\times 2}) = \begin{pmatrix} e^{\frac{1}{\hbar}(a_{11})} & e^{(\frac{1}{\hbar}a_{12r} + i a_{12i})} \\ e^{\frac{1}{\hbar}(a_{12r} - i a_{12i})} & e^{\frac{1}{\hbar}(a_{22})} \end{pmatrix}
$$
(4)

For $\hat{A}_{N\times N}$ we obtain

$$
\exp(\frac{1}{\hbar i}\hat{A}_{N\times N}) = \begin{pmatrix} e^{\frac{1}{\hbar}(a_{11})} & e^{(\frac{1}{\hbar}a_{12r} + i a_{12i})} & \dots & e^{(\frac{1}{\hbar}a_{1Nr} + i a_{1Ni})} \\ e^{\frac{1}{\hbar}(a_{12r} - i a_{12i})} & e^{\frac{1}{\hbar}(a_{22})} & \dots & e^{(\frac{1}{\hbar}a_{2Nr} + i a_{2Ni})} \\ \dots & \dots & \dots & \dots \\ e^{(\frac{1}{\hbar}a_{N1r} - i a_{N1i})} & e^{(\frac{1}{\hbar}a_{N2r} - i a_{N2i})} & \dots & e^{(\frac{1}{\hbar}a_{N,N})} \end{pmatrix}
$$
(5)

Þ ×

K ロ ▶ K 倒 ▶ K 등

Using the above property for matrix of size 2 by 2 we obtain

$$
e^{\frac{1}{i\hbar}\int_{t_0}^t \hat{H}(t_1)dt_1} = \hat{U}(t, t_0) =
$$
\n
$$
\begin{pmatrix}\ne^{\frac{1}{i\hbar}\int_{t_0}^t \hat{H}(t_1)dt_1} & e^{\frac{1}{i\hbar}\int_{t_0}^t t_{sr}(t_1)dt_1 + i\int_{t_0}^t t_{sr}(t_1)dt_1)} \\
e^{\frac{1}{i\hbar}\int_{t_0}^t t_{sr}(t_1)dt_1 - i\int_{t_0}^t t_{sr}(t_1)dt_1} & e^{\frac{1}{i\hbar}\int_{t_0}^t \hat{E}_{p2}(t_1)dt_1}\n\end{pmatrix}
$$
\n(6)

4 0 F

K.P, P.P, .., B.S (UCD) [JJs vs semiconductor qubits](#page-0-0) July 11, 2019 12 / 23

É

イロト イ部 トイモ トイモト

Concept of programmable quantum matter

K.P, P.P, .., B.S (UCD) [JJs vs semiconductor qubits](#page-0-0) July 11, 2019 13 / 23

∢ 口 ≯ ∢ 何

The state of Josephson junction is well described by Bogoliubov-de Gennes equation

$$
\begin{pmatrix} H_0 & \Delta(x) \\ \Delta(x) & -H_0^{\dagger} \end{pmatrix} \begin{pmatrix} u_n(x) \\ v_n(x) \end{pmatrix} = E_n \begin{pmatrix} u_n(x) \\ v_n(x) \end{pmatrix}.
$$
 (7)

Semiconductor single electron line with 2 nodes can be regarded as electrostatic position dependent qubit and can be described by

$$
H_{semi} = t s_{1,2} |1> < 2| + t s_{2,1} |2> < 1| + E_{p1} |1> < 1| + E_{p2} |2> < 2|,
$$

We can express coupling of 2 systems assuming 4 nodes for electron or hole and 2 nodes for electron confined in semiconductor so we have eigenvector having 16 components $|0_{E_e}|E_{S_1}|0_{E_e}|E_{S_2}|E_{S_2}|1_{E_e}$ $|E_{51}>, |1_{F_6}>|E_{52}>, ..., |3_{F_6}>|E_{51}>, |3_{F_6}>|E_{52}>, |0_{F_6}>|E_{51}>$, $|0_{Fe} > |E_{S2} > ... |3_{Fh} > |E_{S1} > |3_{Fh} > |E_{S2} >$.

 QQ

Interace betweem semiconductor qubit and Josephson junction

Josephson junction

electrostatic semiconductor qubit

4 D F

 QQ

Interaction Hamiltonian between semiconductor qubit and Josephson junction

4 D F

 QQ

{Eigenenergies of Josephson junction coupled to SELs(|Δ|=1)} Energy

K.P, P.P, .., B.S (UCD) [JJs vs semiconductor qubits](#page-0-0) July 11, 2019 17 / 23

J.

K ロ ▶ K 御 ▶ K 君 ▶ K 君

÷,

K.P, P.P, .., B.S. (UCD) [JJs vs semiconductor qubits](#page-0-0) July 11, 2019 18/23

重

J.

メロメ (御) メミンメモ

Figure: Eigenenergy spectral of semiconductor qubit coupled to Josephson junction obtained from simplistic tight-binding model (tight-binding BdGe coupled to tight-binding Schroedinger equation for semiconductor qubit).

 Ω

Further extensions of tight-binding model

K.P, P.P, .., B.S (UCD) [JJs vs semiconductor qubits](#page-0-0) July 11, 2019 20/23

4 D F

- Quantum phase transition is expected to occur both in electrostatically coupled semiconductor qubits and systems of coupled Josephson junction to superconducting qubit.
- **•** Increase of superconducting order parameter has similar impact on energy eigenspectrum as the increase of distance between superonducting Josephson junction and semiconductor qubit.

References

[1]. Krzysztof Pomorski, Possible existence of field-induced Josephson junctions, Physica Status Solidi B, 2012.

[2]. Yoshinao Mizugaki, Masafumi Itoh, and Hiroshi Shimada, "Current Correlation in Single-Electron Current Mirror Electromagnetically Dual to Josephson Voltage Mirror", Japanese Journal of Applied Physics, Vol. 46, No. 9B, 2007.

[3]. Jay Gambetta, Jerry Chow, and Matthias Steffen, "Building logical qubits in a superconducting quantum computing system", Nature Partner Journal, Quantum information, Vol. 3, No.2, 2017.

[4]. K.Pomorski, et al, From two types of electrostatic position-dependent semiconductor qubits to quantum universal gates and hybrid semiconductor-superconducting quantum computer, Spie 2019

[5]. K.Pomorski et al, 'Analytic view on coupled single electron lines', arXiv:1904.06822v3, 2019

[6]. Panagiotis Giounanlis et al, Modeling of Semiconductor Electrostatic Qubits Realized Through Coupled Quantum Do[ts,](#page-20-0) [IE](#page-22-0)[E](#page-20-0)[E](#page-21-0) [A](#page-22-0)[c](#page-19-0)[c](#page-20-0)[es](#page-22-0)[s,](#page-19-0)[20](#page-22-0)[19](#page-0-0) QQ

∢ ロ ▶ - ∢ 何 ▶ - ∢ ヨ

To be extended for JJs vs semiconductor qubit interaction: K.Pomorski, Analytical solutions for N interacting electron system con ned in graph of coupled electrostatic quantum dots in tight-binding model, ArXiv: 1907.03180, 2019

 Ω